

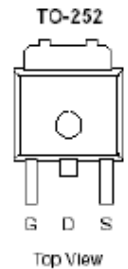
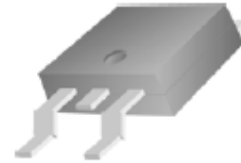
N-Channel 150-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
150	255 @ $V_{GS} = 10V$	12
	290 @ $V_{GS} = 4.5V$	11

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	10	A
Pulsed Drain Current ^b	I_{DM}	50	
Continuous Source Current (Diode Conduction)	I_S	45	A
Power Dissipation	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	50	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

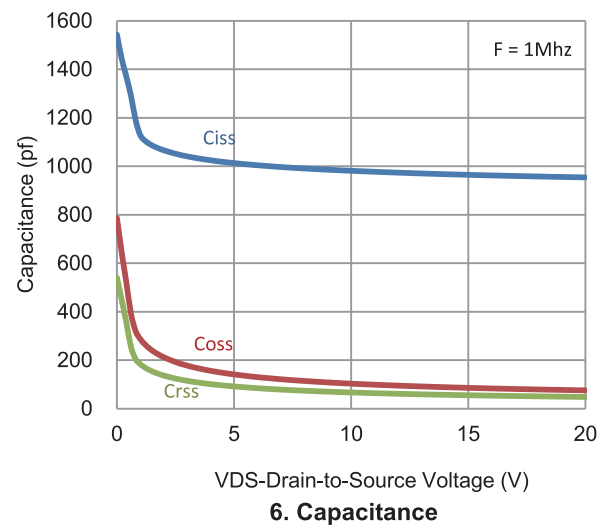
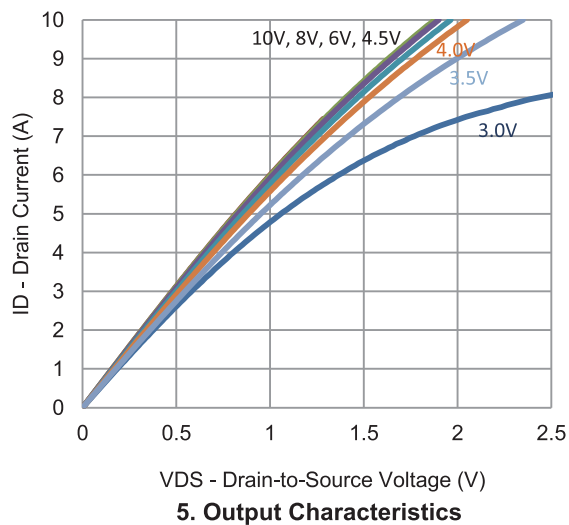
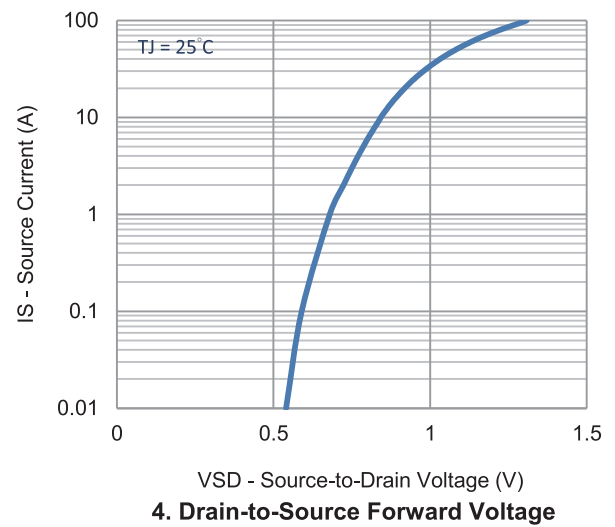
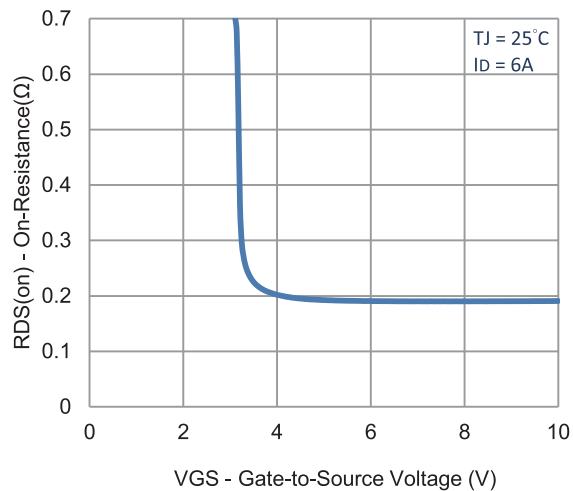
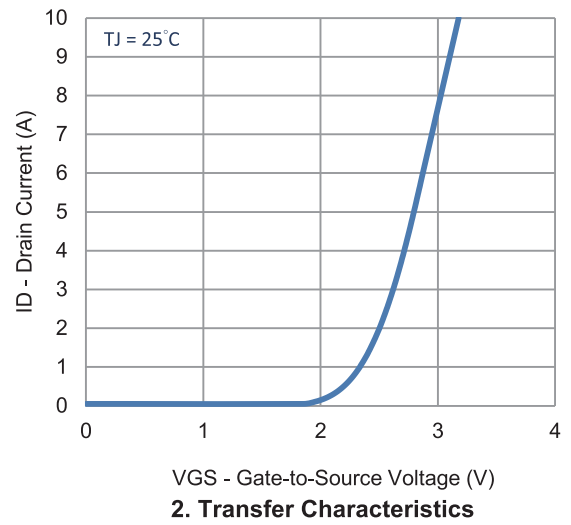
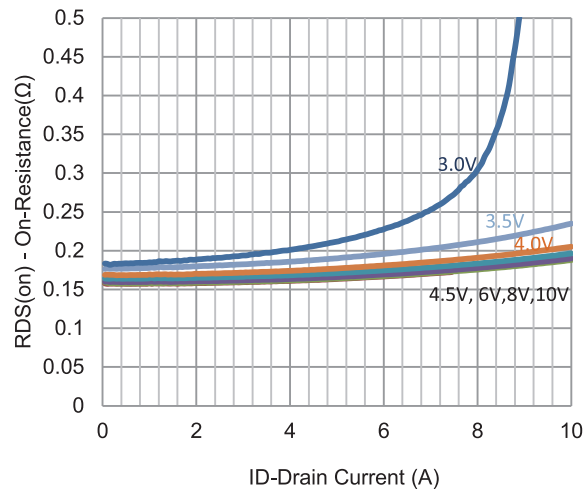
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = 20 V$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 120 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	34			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 6 A$			255	$m\Omega$
		$V_{GS} = 4.5 V, I_D = 5 A$			290	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 6 A$		20		S
Diode Forward Voltage	V_{SD}	$I_S = 25 A, V_{GS} = 0 V$		0.95		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 75 V, V_{GS} = 4.5 V, I_D = 6 A$		16.7		nC
Gate-Source Charge	Q_{gs}			3.5		
Gate-Drain Charge	Q_{gd}			9.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 75 V, R_L = 12.5 \Omega, I_D = 6 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		11		ns
Rise Time	t_r			34		
Turn-Off Delay Time	$t_{d(off)}$			46		
Fall Time	t_f			77		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		965		pF
Output Capacitance	C_{oss}			86		
Reverse Transfer Capacitance	C_{rss}			55		

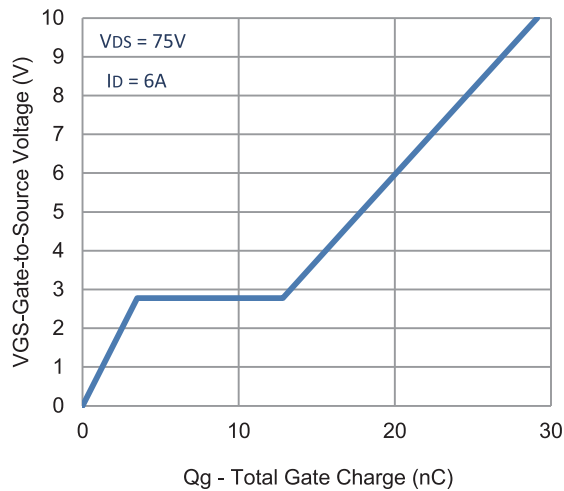
Notes

- Pulse test: PW $\leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

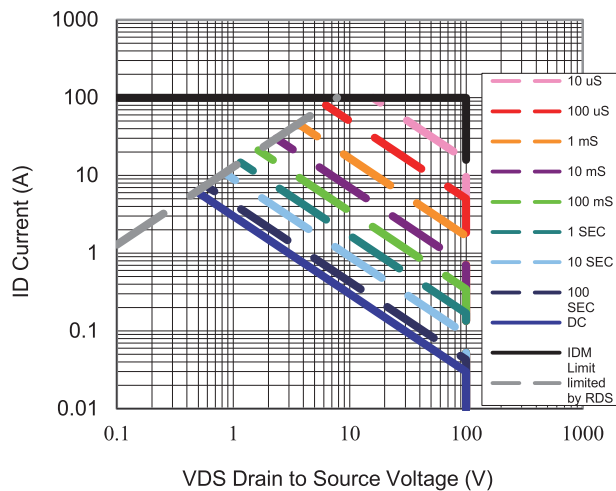
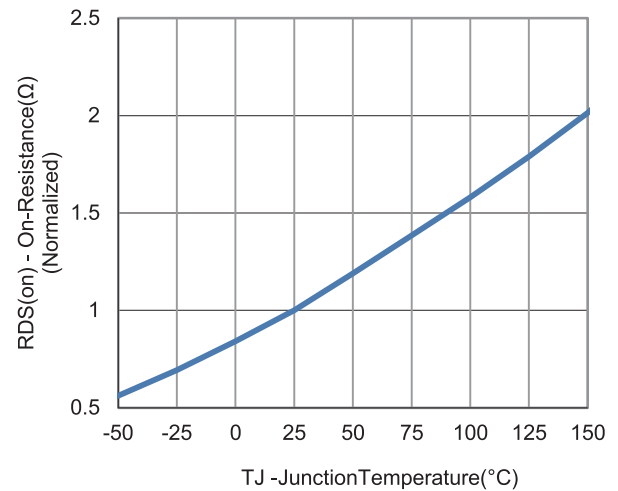
Typical Electrical Characteristics



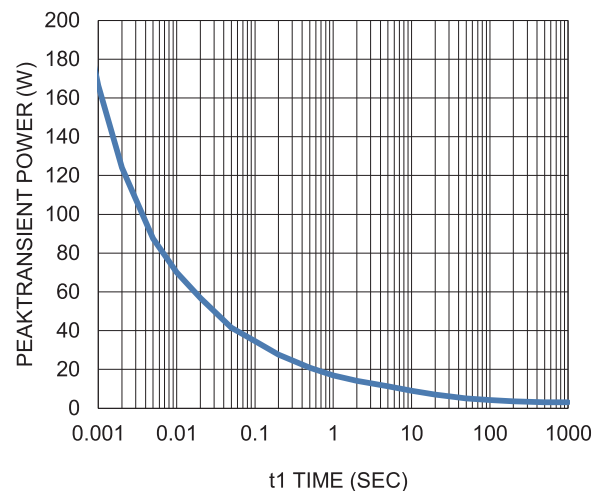
Typical Electrical Characteristics



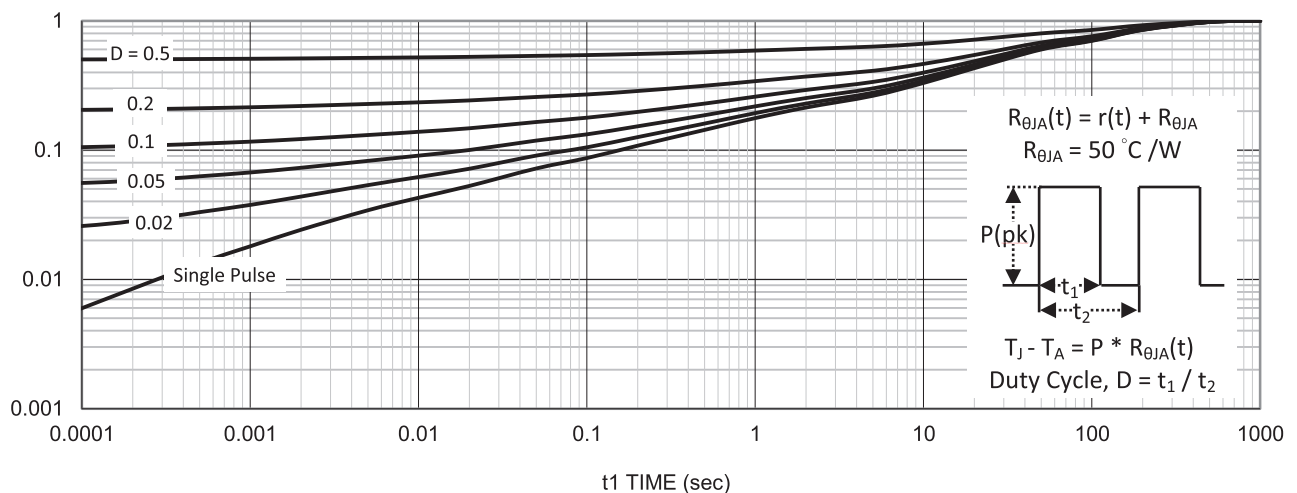
7. Gate Charge



8. Safe Operating Area



9. Single Pulse Maximum Power Dissipation



10. Normalized Thermal Transient Junction to Ambient